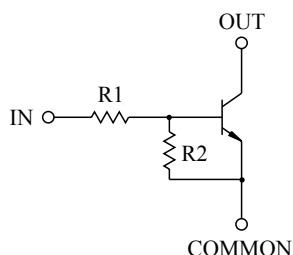


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

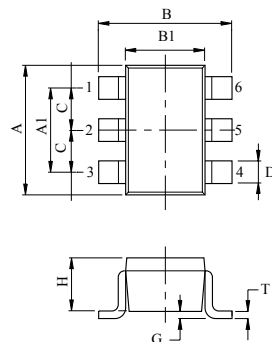
- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.
- High Packing Density.

EQUIVALENT CIRCUIT



BIAS RESISTOR VALUES

TYPE NO.	R1(k Ω)	R2(k Ω)
KRC827U	10	47
KRC828U	22	47
KRC829U	47	22

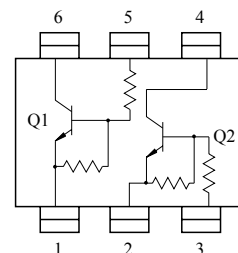


DIM	MILLIMETERS
A	2.00 \pm 0.20
A1	1.3 \pm 0.1
B	2.1 \pm 0.1
B1	1.25 \pm 0.1
C	0.65
D	0.2+0.10/-0.05
G	0-0.1
H	0.9 \pm 0.1
T	0.15+0.1/-0.05

1. Q₁ COMMON (EMITTER)
2. Q₂ COMMON (EMITTER)
3. Q₂ IN (BASE)
4. Q₂ OUT (COLLECTOR)
5. Q₁ IN (BASE)
6. Q₁ OUT (COLLECTOR)

US6

EQUIVALENT CIRCUIT (TOP VIEW)



MAXIMUM RATING (Ta=25°C)

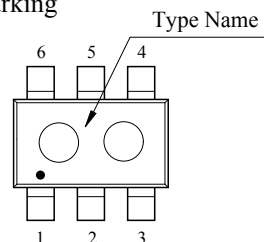
CHARACTERISTIC		SYMBOL	RATING	UNIT
Output Voltage	KRC827U ~ 829U	V _O	50	V
Input Voltage	KRC827U	V _I	30, -6	V
	KRC828U		40, -7	
	KRC829U		40, -15	
Output Current	KRC827U ~ 829U	I _O	100	mA
Power Dissipation		P _D *	200	mW
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	-55 ~ 150	°C

* Total Rating.

MARK SPEC

TYPE	KRC827U	KRC828U	KRC829U
MARK	YH	YI	YJ

Marking



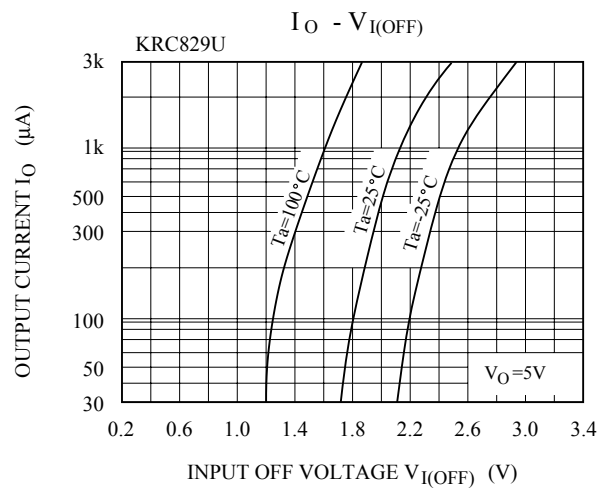
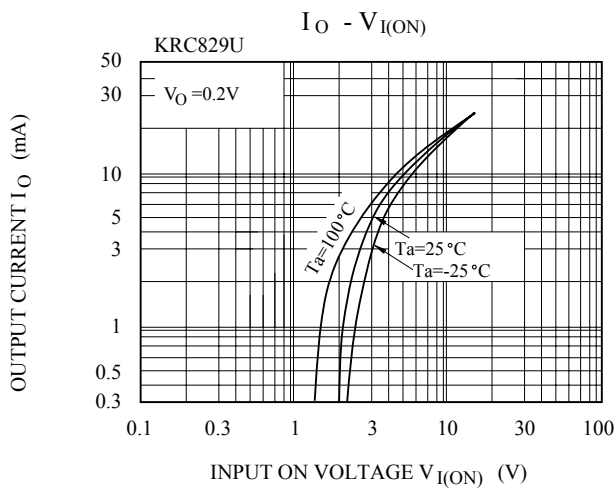
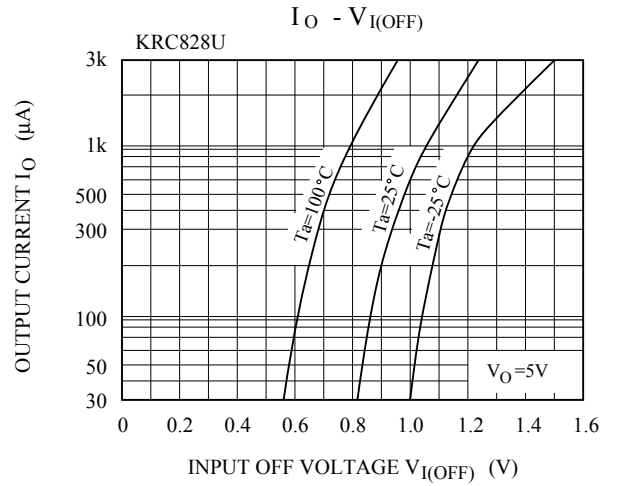
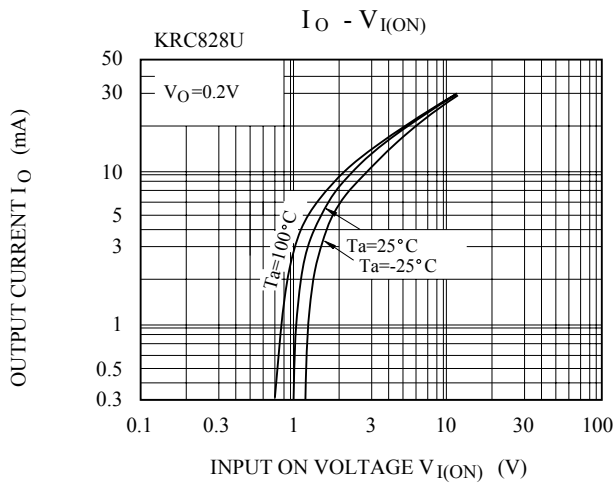
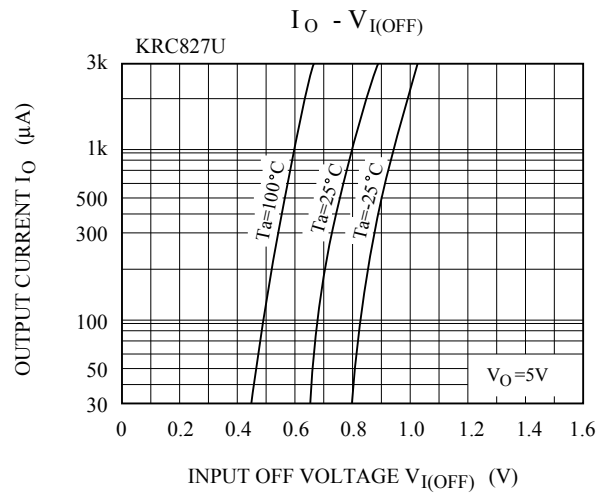
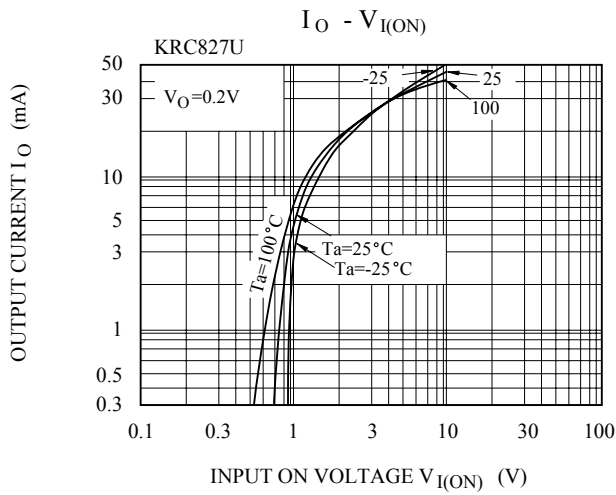
KRC827U~KRC829U

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Output Cut-off Current		KRC827U ~ 829U	I _{O(OFF)}	V _O =50V, V _I =0	-	-	500	nA	
DC Current Gain	KRC827U	G _I	V _O =5V, I _O =10mA	80	150	-			
	KRC828U			80	150	-			
	KRC829U			70	140	-			
Output Voltage		KRC827U ~ 829U	V _{O(ON)}	I _O =10mA, I _I =0.5mA	-	0.1	0.3	V	
Input Voltage (ON)	KRC827U	V _{I(ON)}	V _O =0.2V, I _O =5mA	-	1.2	1.8	V		
	KRC828U			-	1.8	2.6			
	KRC829U			-	3.0	5.8			
Input Votlage (OFF)	KRC827U	V _{I(OFF)}	V _O =5V, I _O =0.1mA	0.5	0.75	-	V		
	KRC828U			0.6	0.88	-			
	KRC829U			1.5	1.82	-			
Transition Frequency		KRC827U ~ 829U	f _I *	V _O =10V, I _O =5mA	-	200	-	MHz	
Input Current		KRC827U	I _I	V _I =5V	-	-	0.88	mA	
		KRC828U			-	-	0.36		
		KRC829U			-	-	0.16		
Switching Time	Rise Time	KRC827U	t _r	V _O =5V, V _{IN} =5V R _L =1kΩ	-	0.05	-	μS	
		KRC828U			-	0.12	-		
		KRC829U			-	0.26	-		
	Storage Time	KRC827U			t _{stg}	-	2.0		-
		KRC828U				-	2.4		-
		KRC829U				-	1.5		-
	Fall Time	KRC827U			t _f	-	0.36		-
		KRC828U				-	0.4		-
		KRC829U				-	0.41		-

Note : * Characteristic of Transistor Only.

KRC827U~KRC829U



KRC827U~KRC829U

